



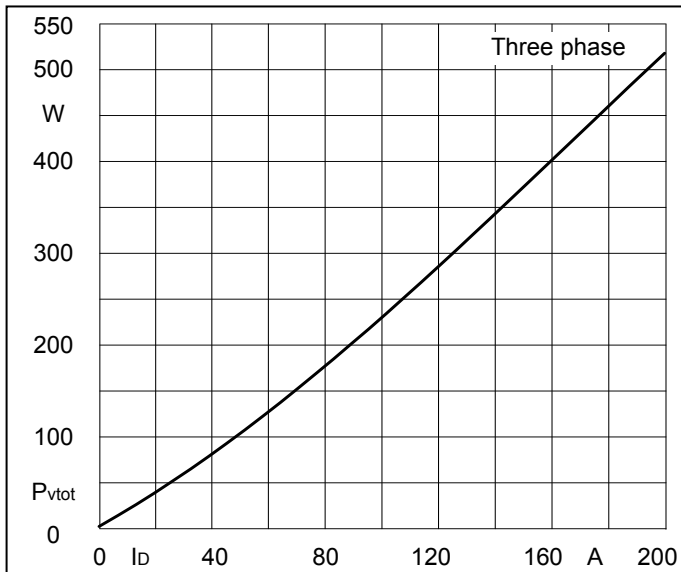
## ◆ Thyristor Maximum Ratings

Symbol	Item	Conditions	Values	Units
$I_{TAV}$	Average On-State Current	$T_c=93^{\circ}\text{C}$ , Single Phase half wave 180° conduction	200	A
$I_{TSM}$	Surge On-State Current	$T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$ (50Hz), sine $VR=0$	1900	A
$i^2t$	Circuit Fusing Consideration		18050	$\text{A}^2\text{s}$
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1 min	3000	V
$T_{vj}$	Operating Junction Temperature		-40 to +125	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature		-40 to +125	$^{\circ}\text{C}$
Mt	Mounting Torque	To terminals(M4)	$2\pm 15\%$	Nm
Mt		To terminals(M6)	$5\pm 15\%$	
Ms		To heatsink(M6)	$5\pm 15\%$	Nm
di/dt	Critical Rate of Rise of On-State Current	$T_{VJ}=T_{VJM}$ , $V_D=1/2V_{DRM}$ , $I_G=100\text{mA}$ $d_{iG}/d_t=0.1\text{A}/\mu\text{s}$	200	$\text{A}/\mu\text{s}$
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_J=T_{VJM}$ , $V_D=2/3V_{DRM}$ , linear voltage rise	500	$\text{V}/\mu\text{s}$

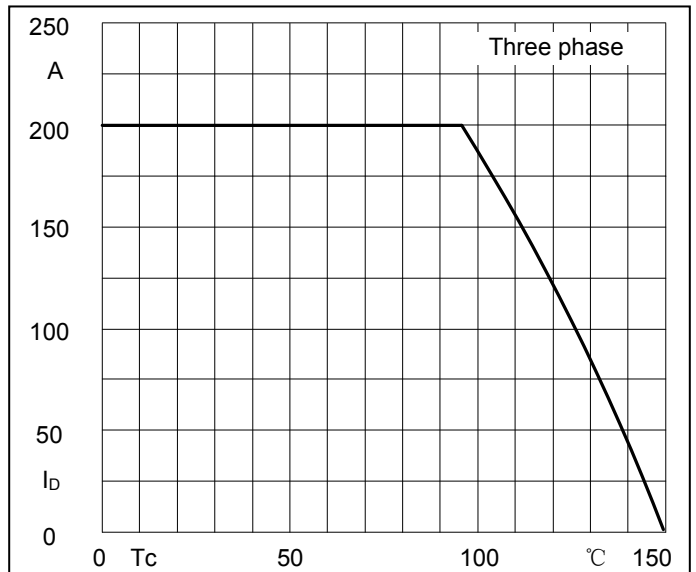
## Electrical and Thermal Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
$V_{TM}$	Peak On-State Voltage, max.	$T=25^{\circ}\text{C}$ $I_T=600\text{A}$			1.80	V
$I_{RRM}/I_{DRM}$	Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max.	$T_{VJ}=T_{VJM}$ , $V_R=V_{RRM}$ , $V_D=V_{DRM}$			100	mA
$V_{GT}$	Gate Trigger Voltage, max.	$T_{VJ}=25^{\circ}\text{C}$ , $V_D=6\text{V}$			3	V
$I_{GT}$	Gate Trigger Current, max.	$T_{VJ}=25^{\circ}\text{C}$ , $V_D=6\text{V}$			150	mA
Rth(j-c)	Thermal Impedance, max.	Junction to Case			0.14	$^{\circ}\text{C}/\text{W}$
Rth(c-s)	Thermal Impedance, max.	Case to Heatsink			0.06	$^{\circ}\text{C}/\text{W}$

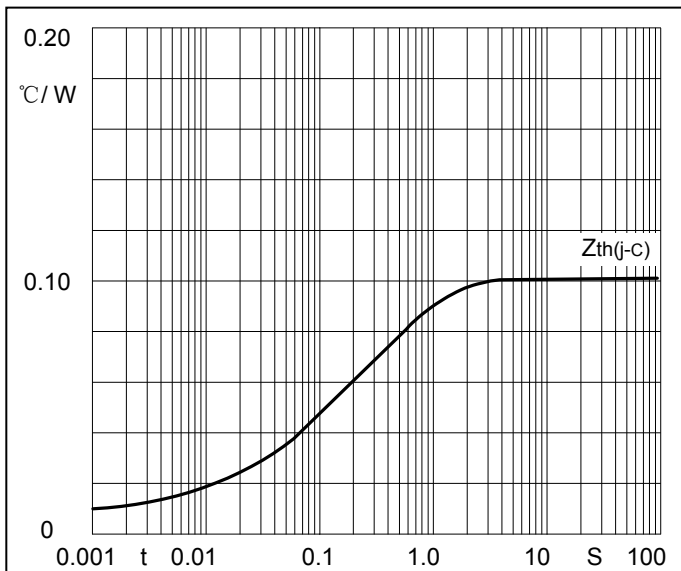
## Performance Curves



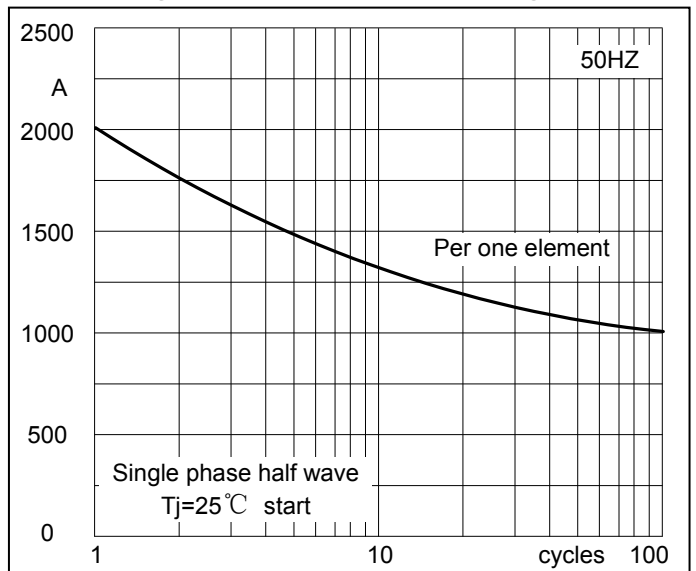
**Fig1. Power dissipation**



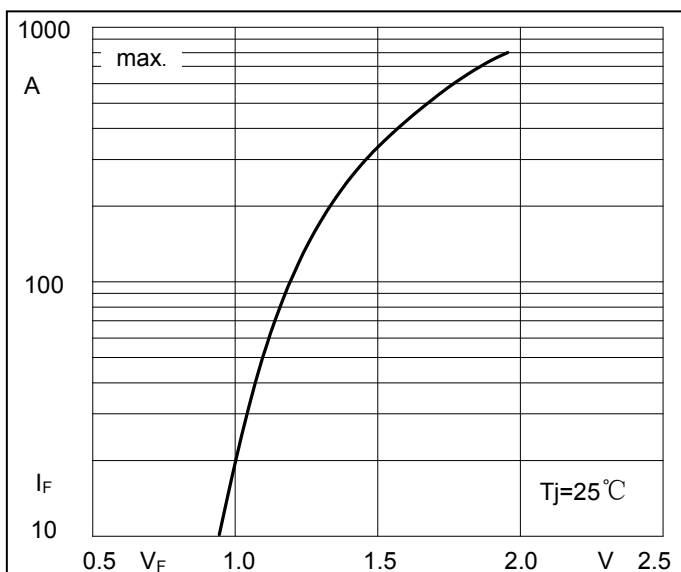
**Fig2. Forward Current Derating Curve**



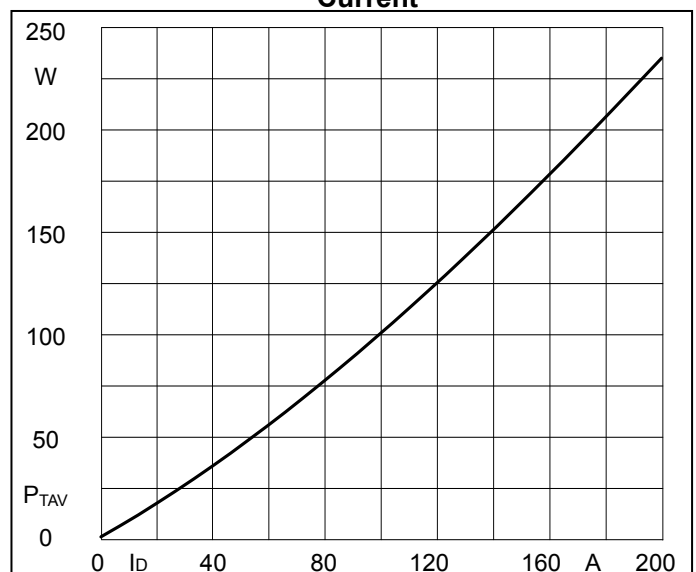
**Fig3. Transient thermal impedance**



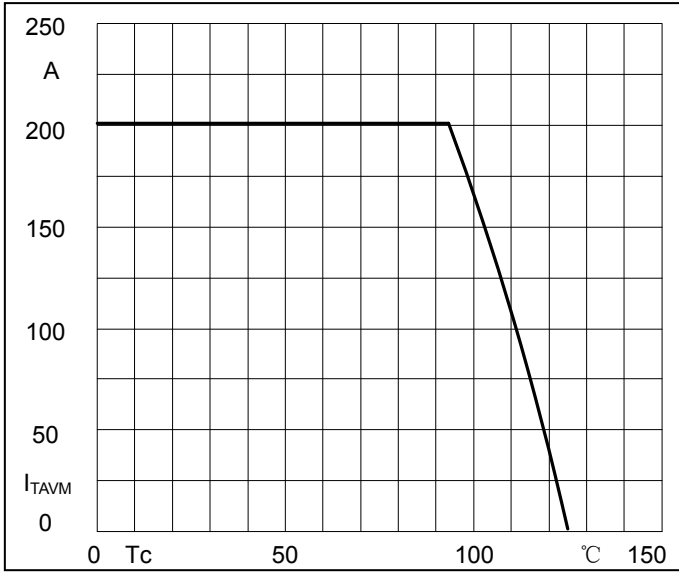
**Fig4. Max Non-Repetitive Forward Surge Current**



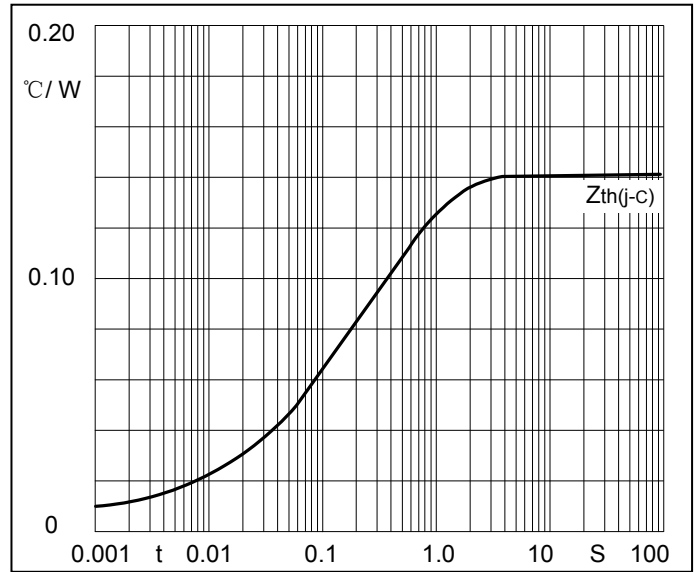
**Fig5. Forward Characteristics**



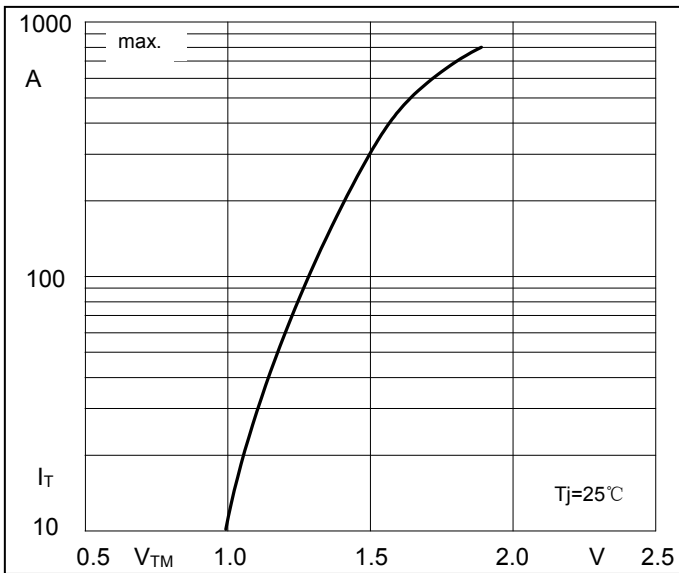
**Fig6. SCR Power dissipation**



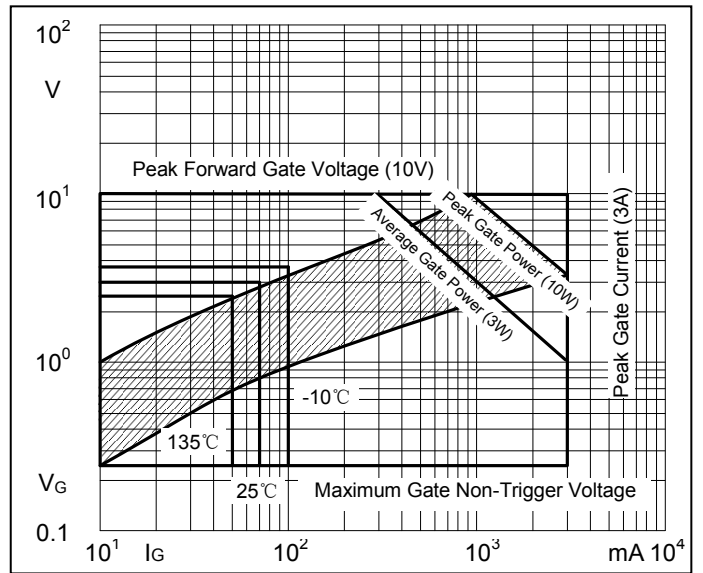
**Fig7. SCR Forward Current Derating Curve**



**Fig8. SCR Transient thermal impedance**

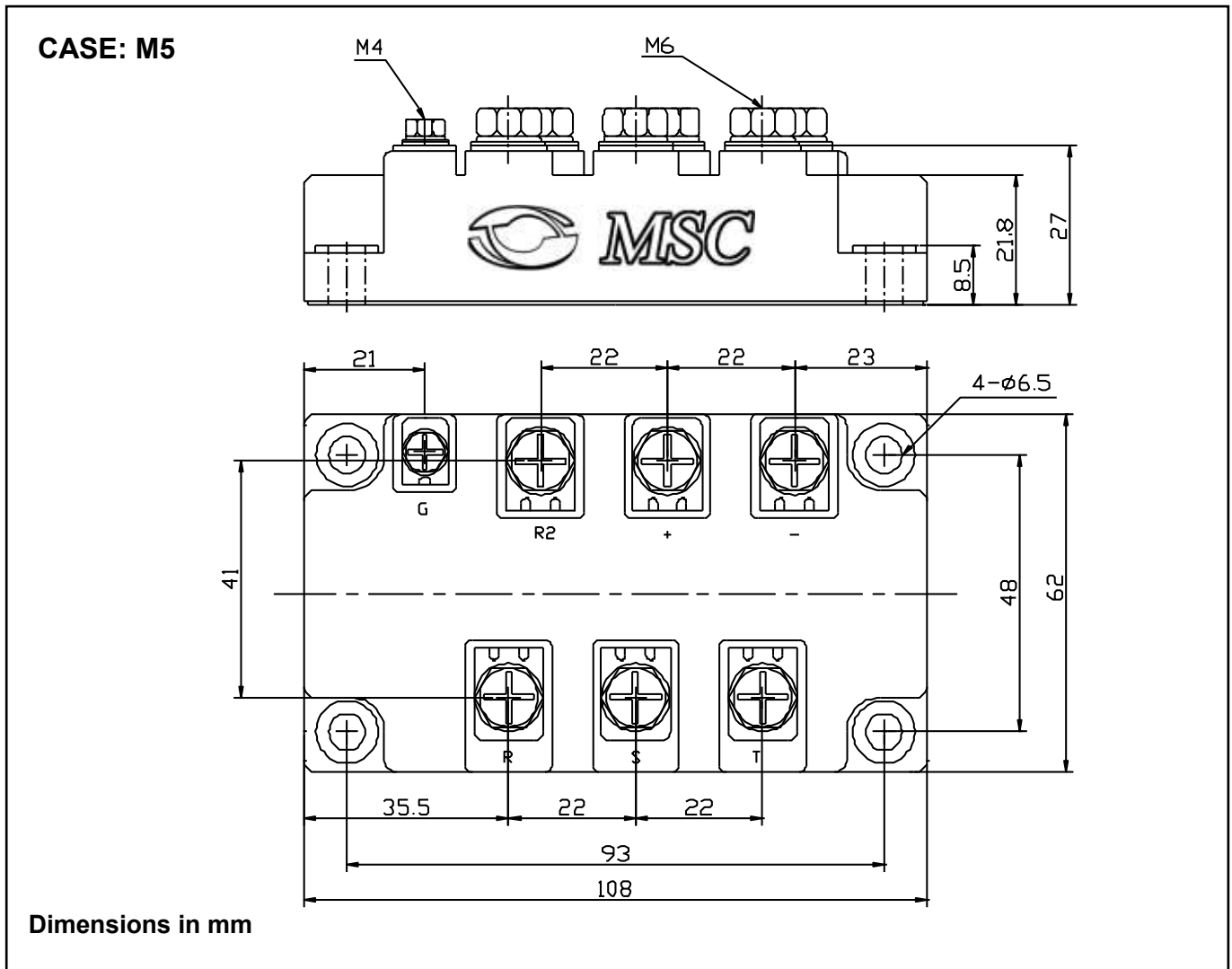


**Fig9. SCR Forward Characteristics**



**Fig10. Gate trigger Characteristics**

## Package Outline Information



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[25.330.4753.1](#) [25.330.5253.1](#) [25.334.3253.1](#) [25.334.3353.1](#) [25.350.2053.0](#) [25.352.4753.1](#) [25.522.3253.0](#) [T483C](#) [T484C](#) [T485F](#) [T485H](#)  
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[25.640.5053.0](#)